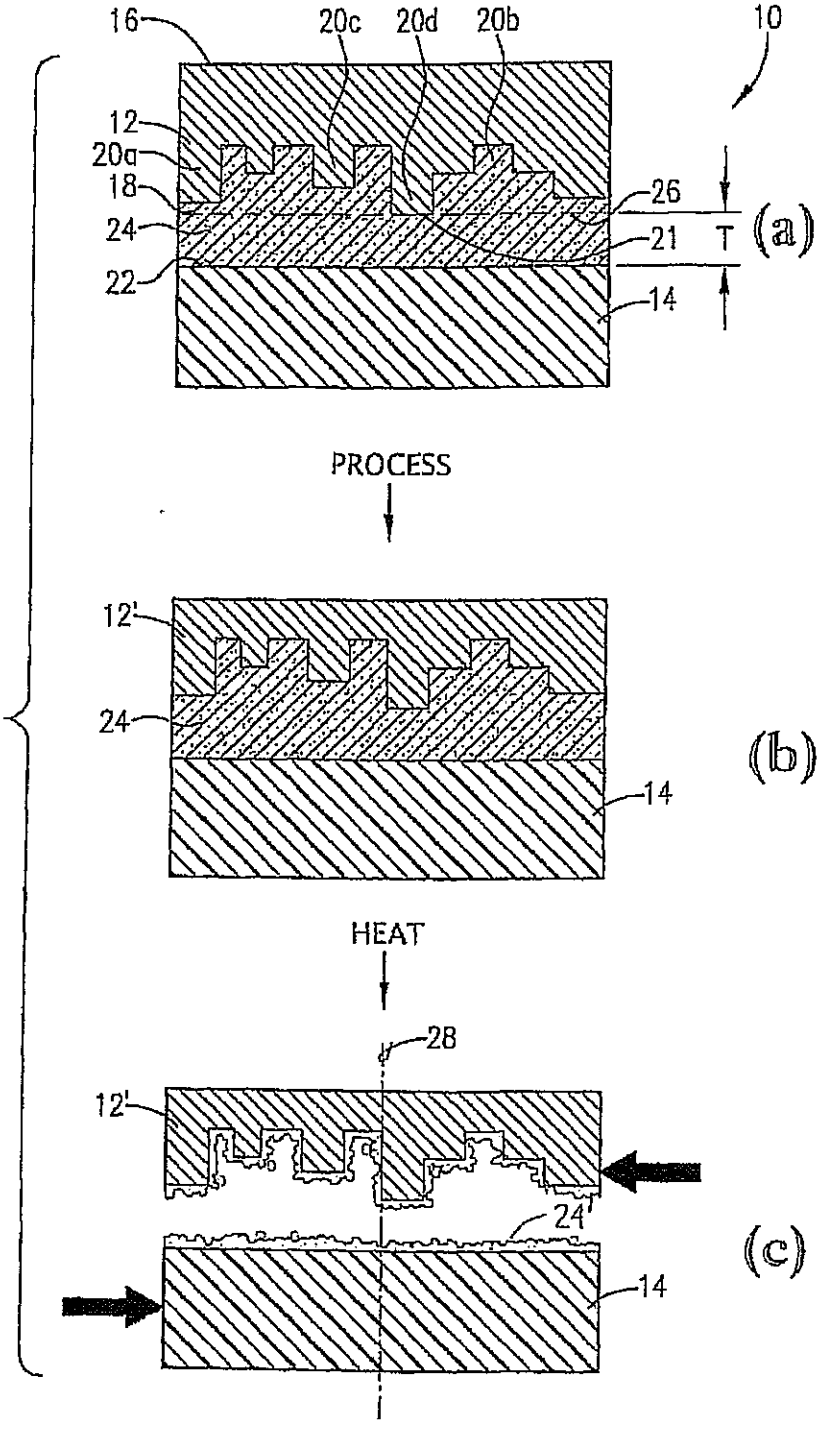

16
20c
20d
20b
10
12
20a
18
24
22
26
21
T
(a)
14
PROCESS
12'
24
(b)
14
HEAT
28
12'
24'
(c)
14

FIG. 1

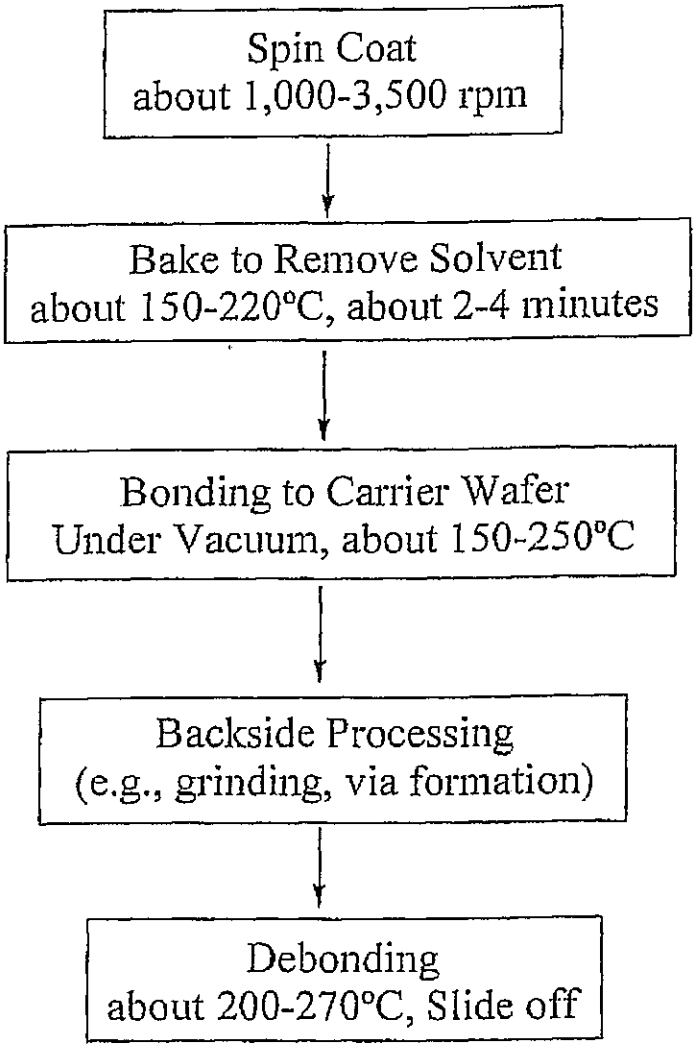

Spin Coat
about 1,000-3,500 rpm
Bake to Remove Solvent
about 150-220°C, about 2-4 minutes
Bonding to Carrier Wafer
Under Vacuum, about 150-250°C
Backside Processing
(e.g., grinding, via formation)
Debonding
about 200-270°C, Slide off

Fig. 2

Fig. 3

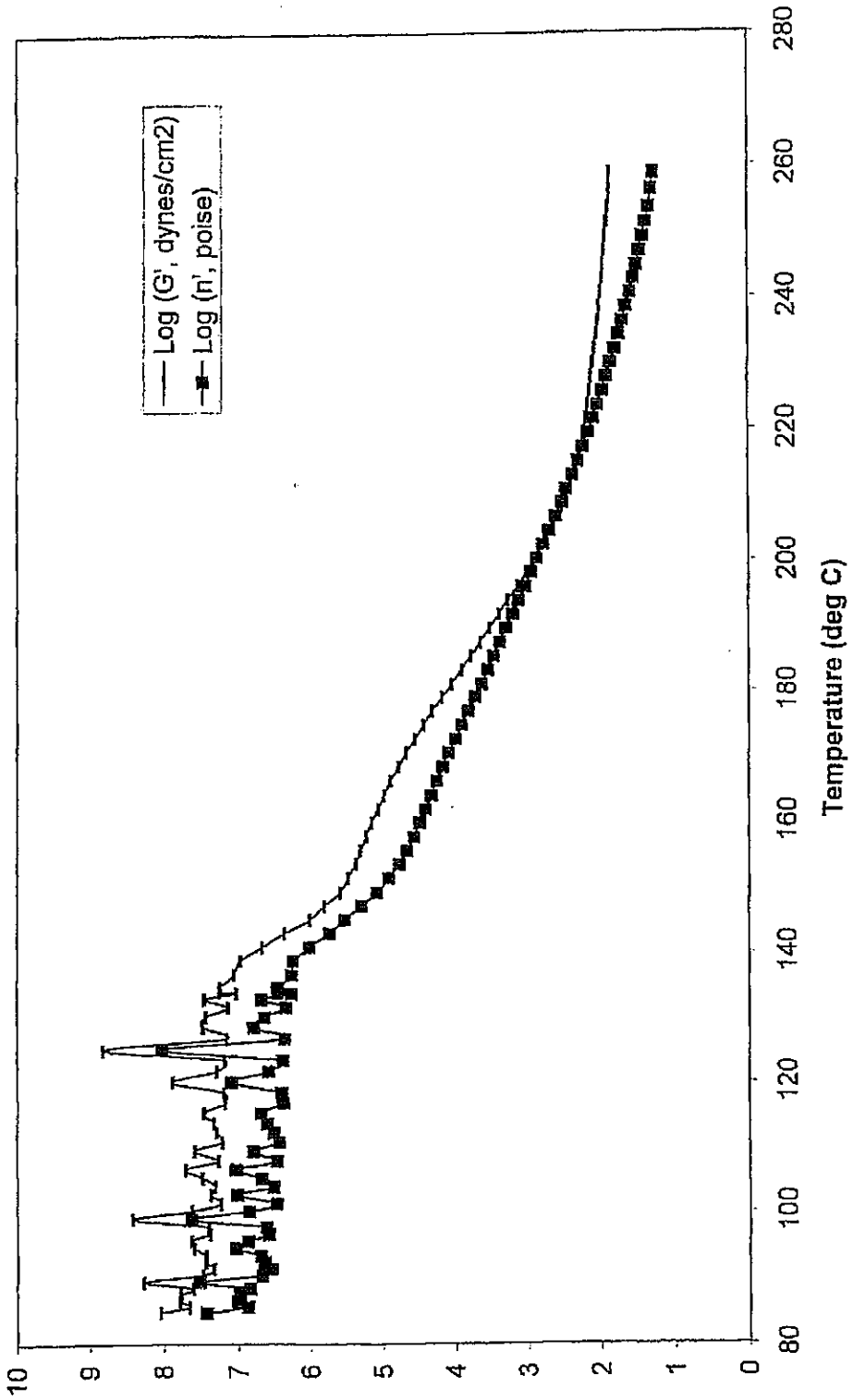

Log (G', dynes/cm2)
Log (n', poise)
10
9
8
7
6
5
4
3
2
1
0
80
100
120
140
160
180
200
220
240
260
280
Temperature (deg C)

Fig. 4

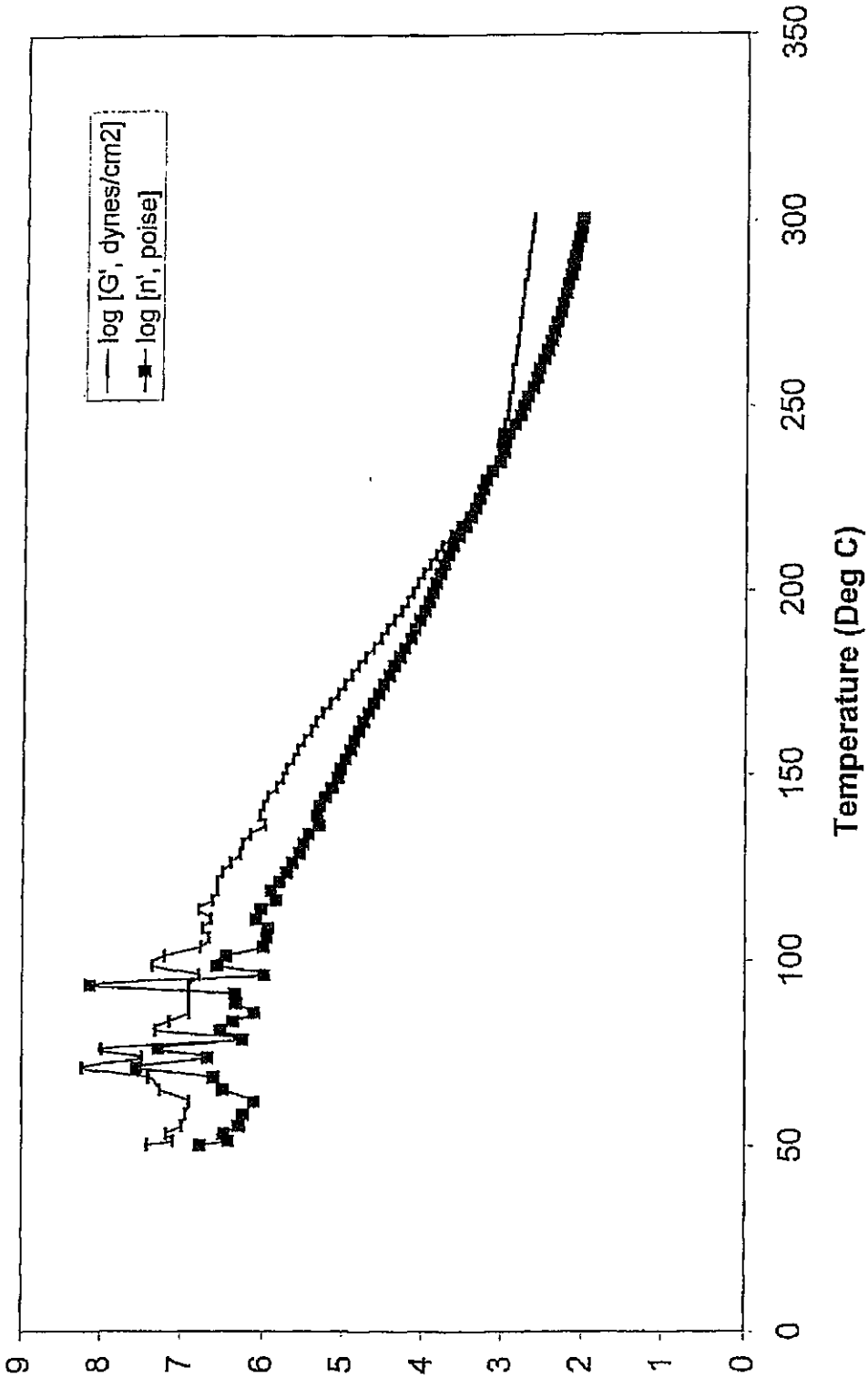

log [G', dynes/cm2]
log [n', poise]
0
1
2
3
4
5
6
7
8
9
0
50
100
150
200
250
300
350
Temperature (Deg C)

Fig. 5

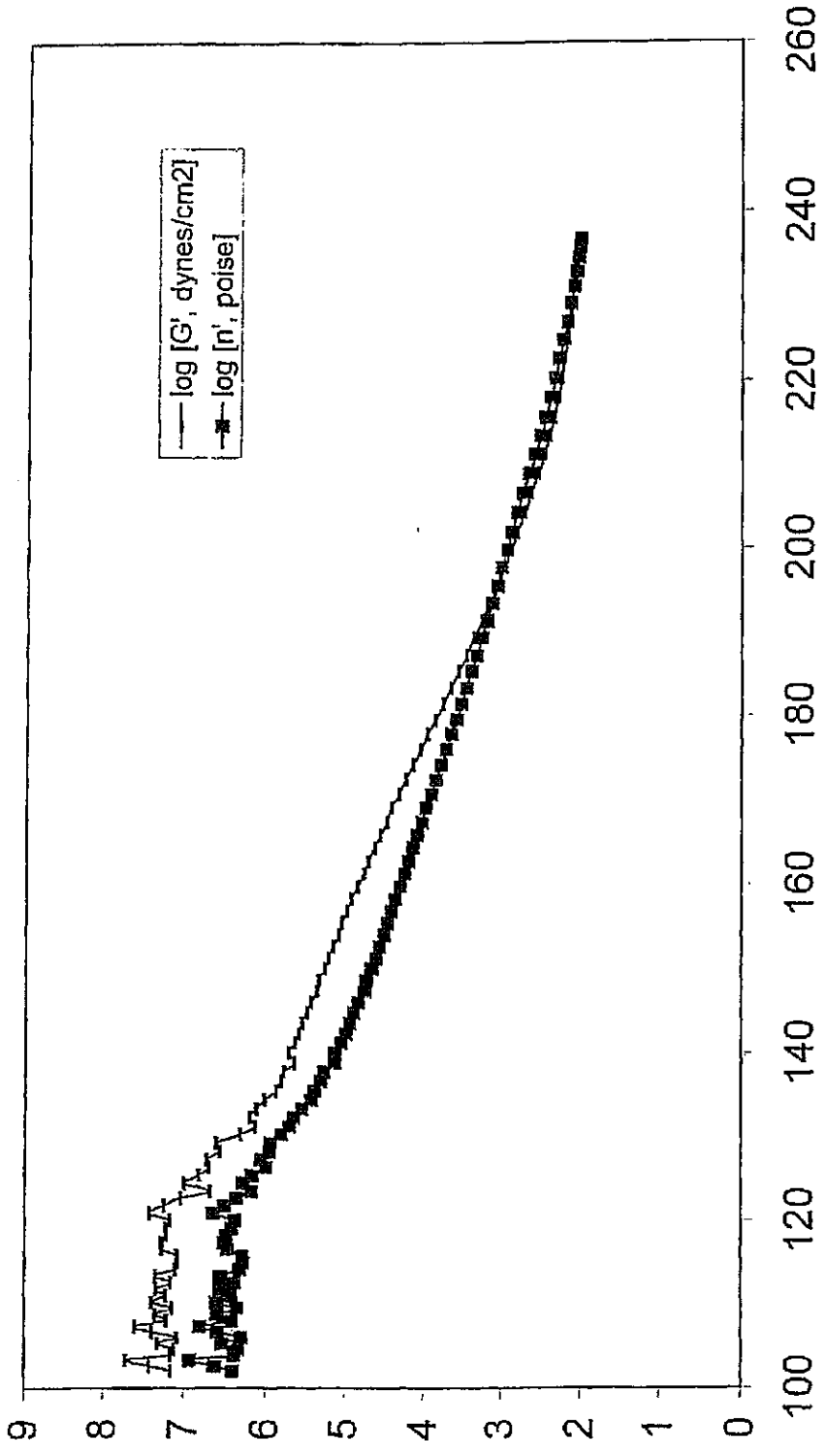
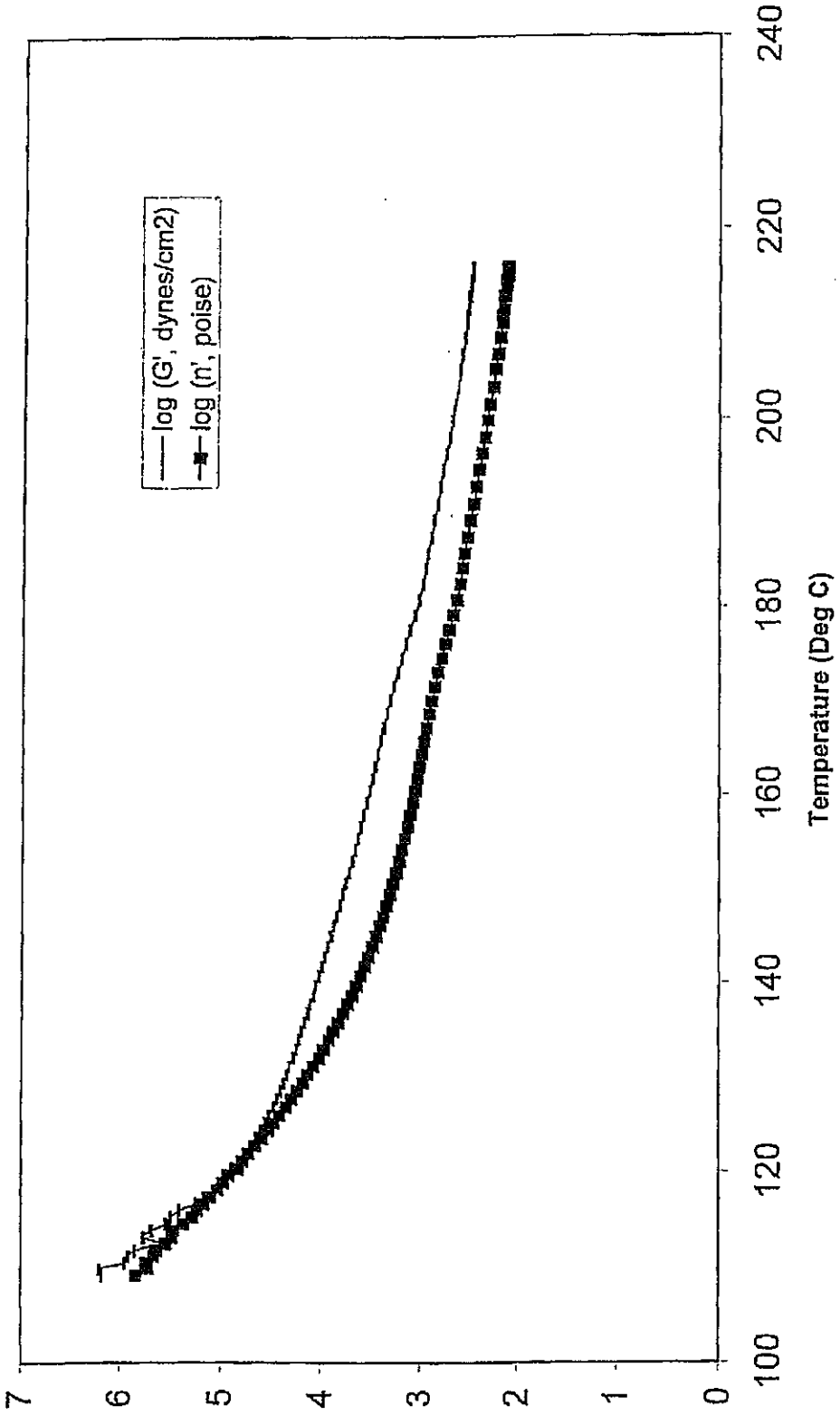

log [G', dynes/cm2]
log [n', poise]
9
8
7
6
5
4
3
2
1
0
100
120
140
160
180
200
220
240
260
Temperature (Deg C)

Fig. 6


log (G', dynes/cm2)
log (n', poise)
0
1
2
3
4
5
6
7
100
120
140
160
180
200
220
240
Temperature (Deg C)